

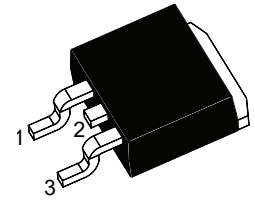
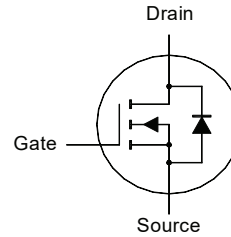
N-Channel Enhancement Mode MOSFET

Features

- Low Gate Charge
- Low $R_{DS(ON)}$
- Halogen and Antimony Free(HAF), RoHS compliant

Applications

- For Flyback topologies for example used in Chargers, Adapters, Lighting etc.



1.Gate 2.Drain 3.Source
TO-263 Plastic Package

Key Parameters

Parameter	Value	Unit
BV_{DSS}	650	V
$R_{DS(ON)}$ Max	190 @ $V_{GS} = 10$ V	m Ω
$V_{GS(th)}$ typ	3	V
Q_g typ	46 @ $V_{GS} = 10$ V	nC

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 30	V
Drain Current	I_D	$T_c = 25^\circ\text{C}$ 19.5 $T_c = 100^\circ\text{C}$ 12	A
Peak Drain Current, Pulsed ¹⁾	I_{DM}	65	A
Single-Pulse Avalanche Current	I_{AS}	4.9	A
Single-Pulse Avalanche Energy ²⁾	E_{AS}	948.3	mJ
Total Power Dissipation	P_{tot}	156	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.8	$^\circ\text{C/W}$
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	35	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width ≤ 100 μs , Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 79$ mH, $R_g = 25$ Ω , $I_{AS} = 4.9$ A, $V_{GS} = 10$ V.

³⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 250 \mu\text{A}$	BV_{DSS}	650	-	-	V
Drain-Source Leakage Current at $V_{DS} = 650 \text{ V}, V_{GS} = 0 \text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current at $V_{GS} = \pm 30 \text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance at $V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	$R_{DS(on)}$	-	149	190	m Ω
DYNAMIC PARAMETERS					
Forward Transconductance at $V_{DS} = 20 \text{ V}, I_D = 10 \text{ A}$	g_{fs}	-	11	-	S
Gate Resistance at $V_{DS} = 0 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	R_g	-	1.2	-	Ω
Input Capacitance at $V_{GS} = 0 \text{ V}, V_{DS} = 300 \text{ V}, f = 1 \text{ MHz}$	C_{iss}	-	1476	-	pF
Output Capacitance at $V_{GS} = 0 \text{ V}, V_{DS} = 300 \text{ V}, f = 1 \text{ MHz}$	C_{oss}	-	65	-	pF
Reverse Transfer Capacitance at $V_{GS} = 0 \text{ V}, V_{DS} = 300 \text{ V}, f = 1 \text{ MHz}$	C_{rss}	-	9	-	pF
Gate Charge Total at $V_{DS} = 350 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	Q_g	-	46	-	nC
Gate to Source Charge at $V_{DS} = 350 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	Q_{gs}	-	9	-	nC
Gate to Drain Charge at $V_{DS} = 350 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	Q_{gd}	-	21	-	nC
Turn-On Delay Time at $V_{DD} = 350 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}, R_G = 24 \Omega$	$t_{d(on)}$	-	60	-	ns
Turn-On Rise Time at $V_{DD} = 350 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}, R_G = 24 \Omega$	t_r	-	18	-	ns
Turn-Off Delay Time at $V_{DD} = 350 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}, R_G = 24 \Omega$	$t_{d(off)}$	-	60	-	ns
Turn-Off Fall Time at $V_{DD} = 350 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}, R_G = 24 \Omega$	t_f	-	28	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $V_{GS} = 0 \text{ V}, I_S = 20 \text{ A}$	V_{SD}	-	-	1.2	V
Body-Diode Continuous Current	I_S	-	-	19.5	A
Pulsed Body-Diode Continuous Current	I_{SM}	-	-	65	A
Body Diode Reverse Recovery Time at $I_S = 10 \text{ A}, di/dt = 100 \text{ A} / \mu\text{s}$	t_{rr}	-	365	-	ns
Body Diode Reverse Recovery Charge at $I_S = 10 \text{ A}, di/dt = 100 \text{ A} / \mu\text{s}$	Q_{rr}	-	5.5	-	μC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

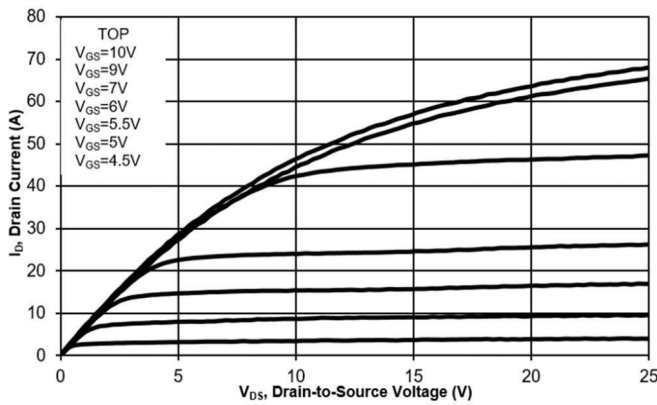


Fig. 2 Typical Transfer Characteristics

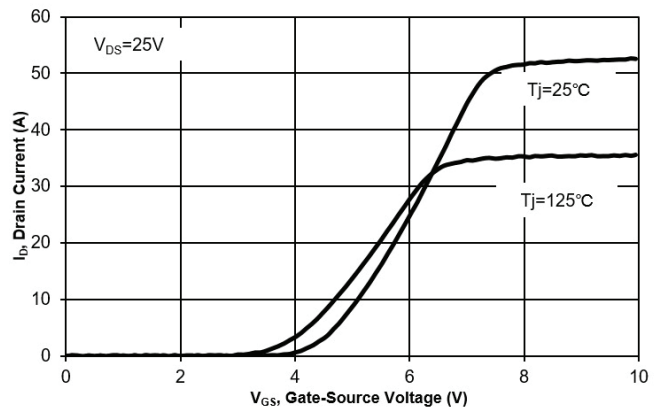


Fig. 3 On-Resistance vs. Drain Current

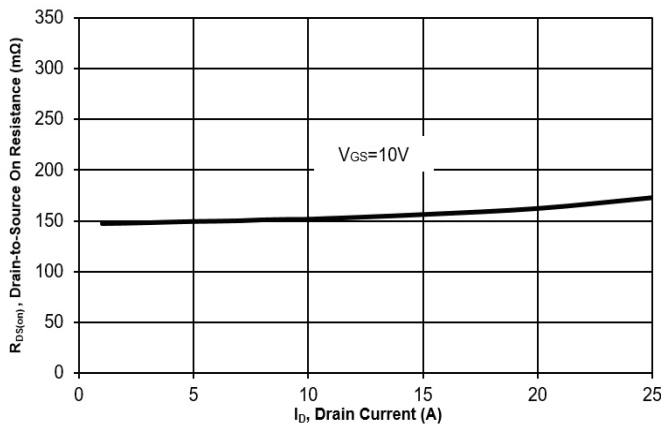


Fig. 4 On-Resistance vs. Gate to Source Voltage

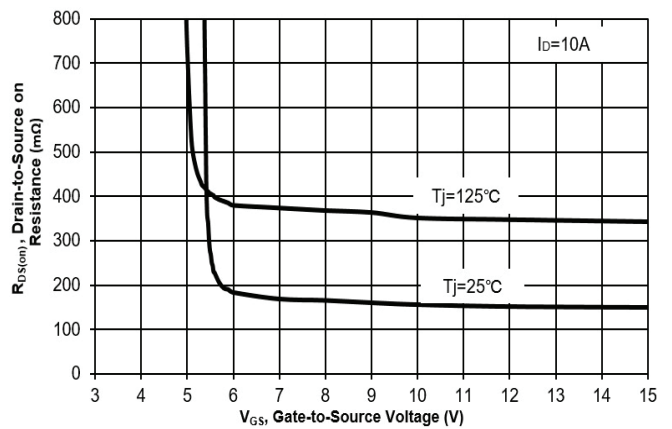


Fig. 5 On-Resistance vs. Tj

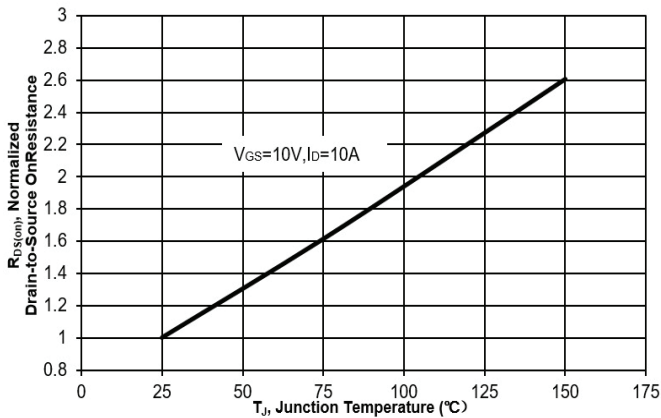
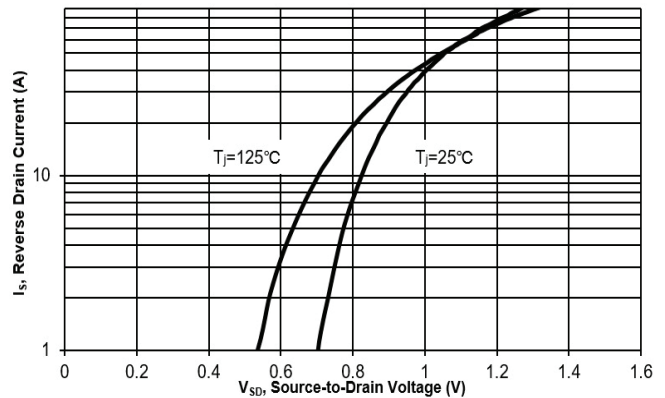


Fig. 6 Typical Body-Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

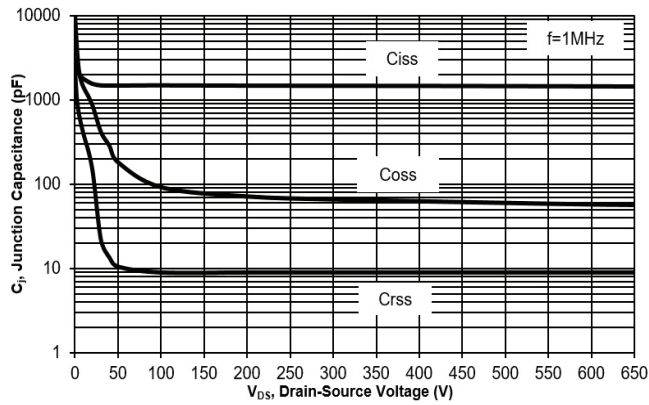


Fig. 8 Drain-Source Leakage Current vs. T_J

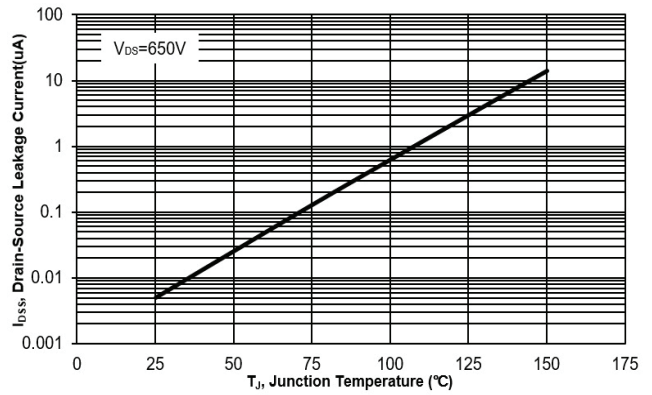


Fig. 9 V_{(BR)DSS} vs. Junction Temperature

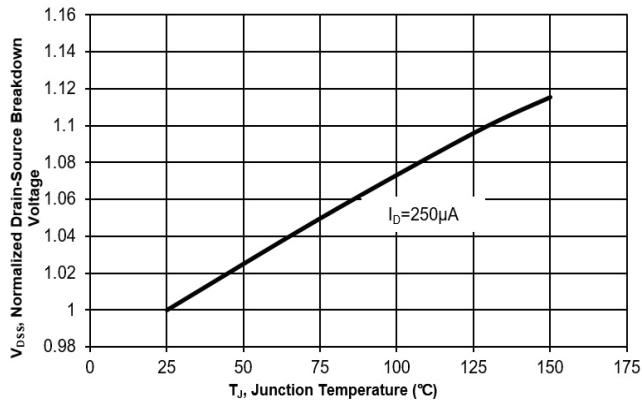


Fig. 10 Gate Threshold Variation vs. T_J

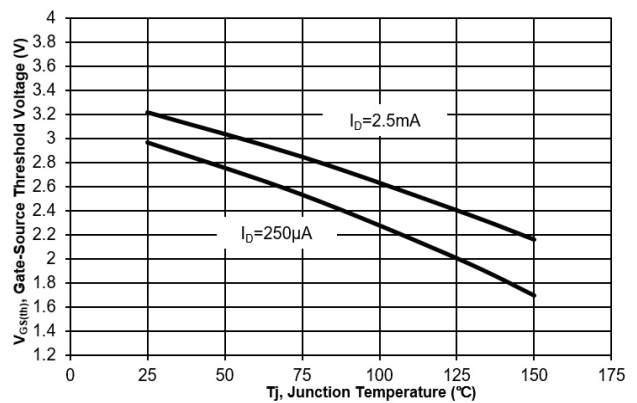


Fig. 11 Gate Charge

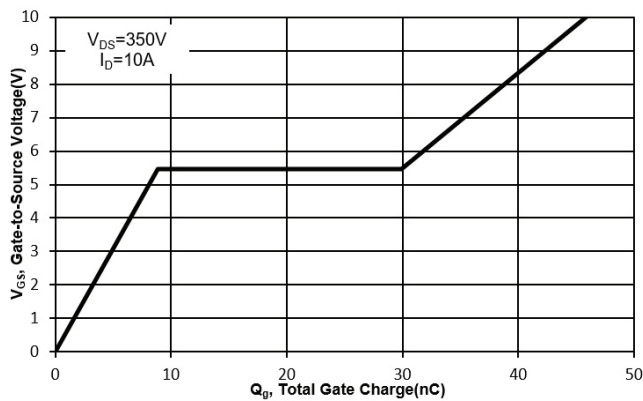


Fig. 12 Safe Operation Area

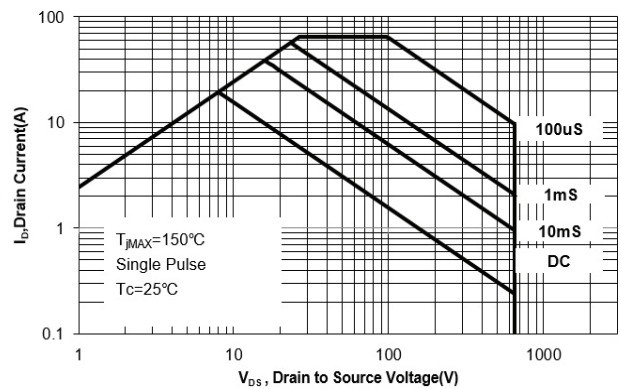


Fig. 13 Normalized Maximum Transient Thermal Impedance($z_{\theta JC}$)

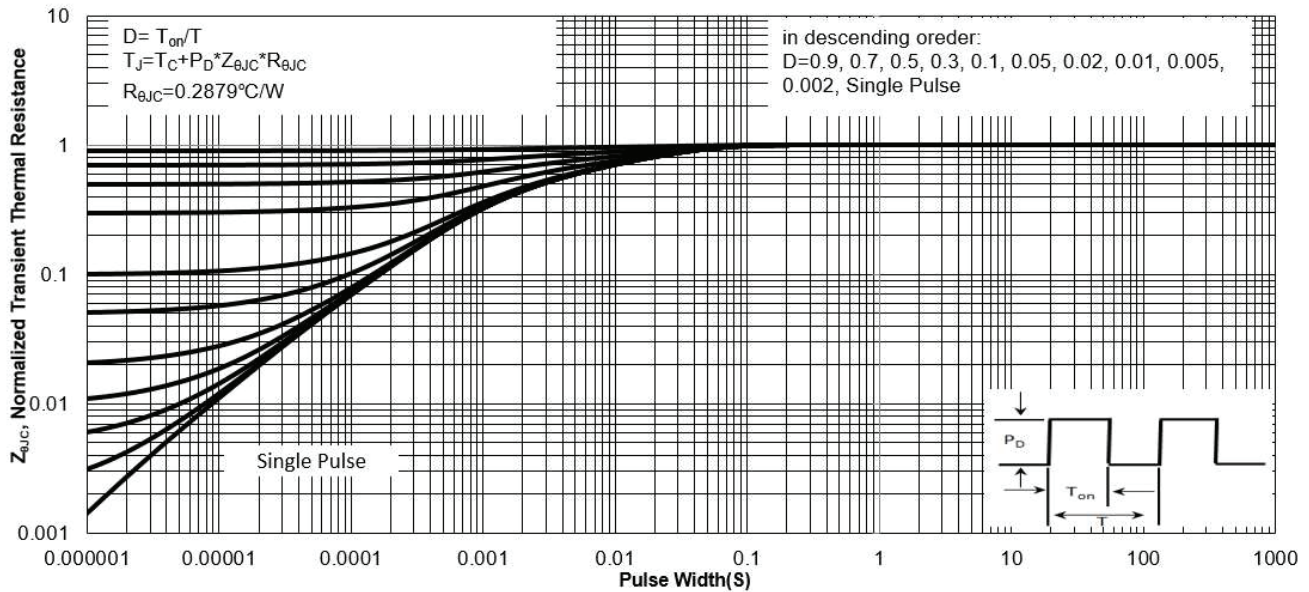
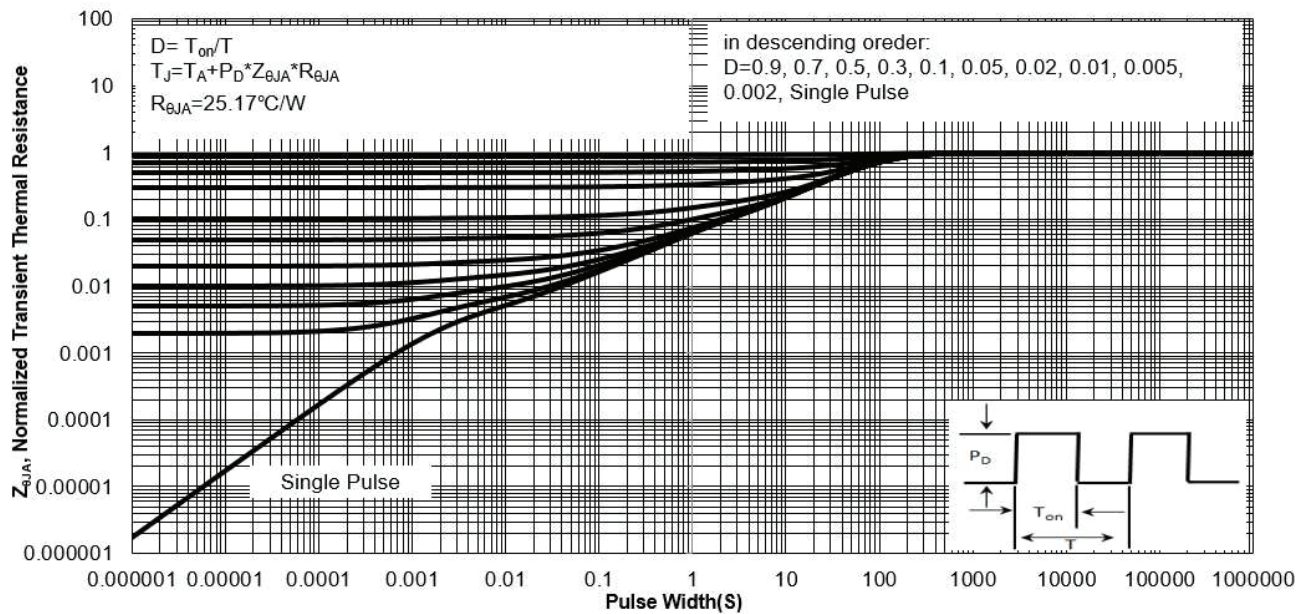


Fig. 14 Normalized Maximum Transient Thermal Impedance($z_{\theta JA}$)



Test Circuits

Fig.1-1 Switching times test circuit

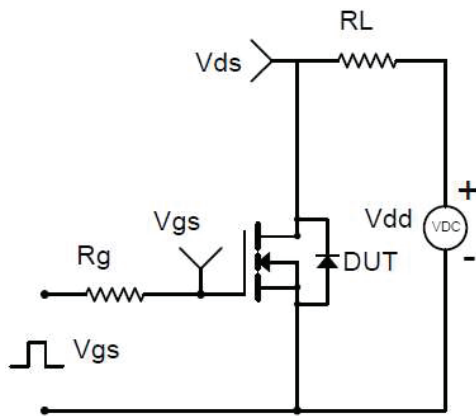


Fig.1-2 Switching Waveform

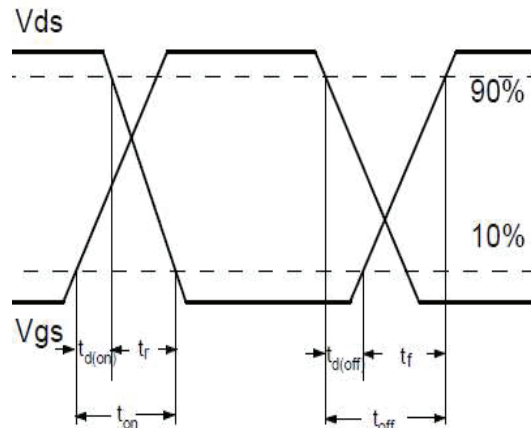


Fig.2-1 Gate charge test circuit

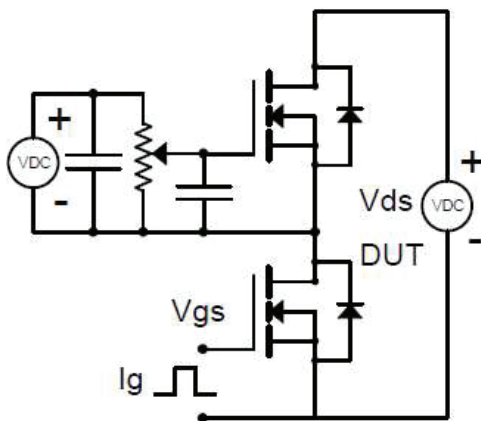


Fig.2-2 Gate charge waveform

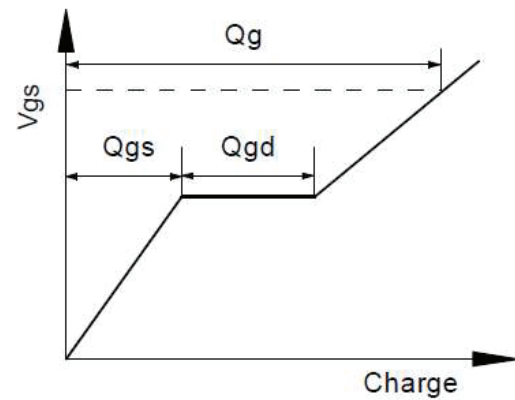


Fig.3-1 Avalanche test circuit

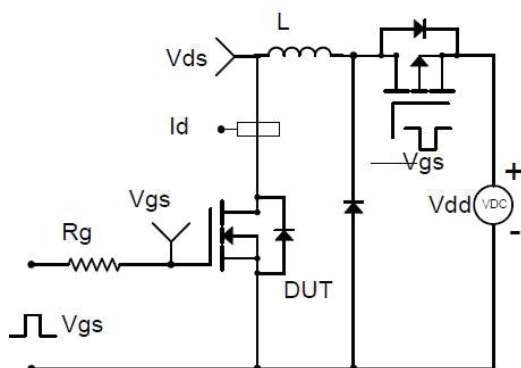
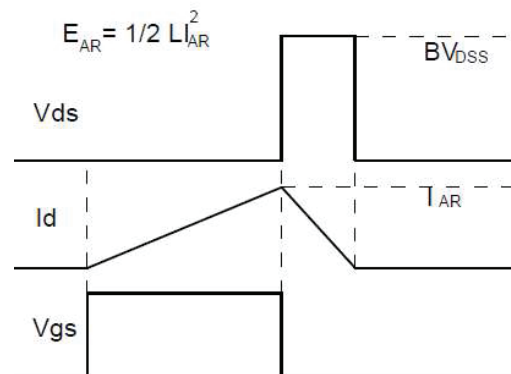
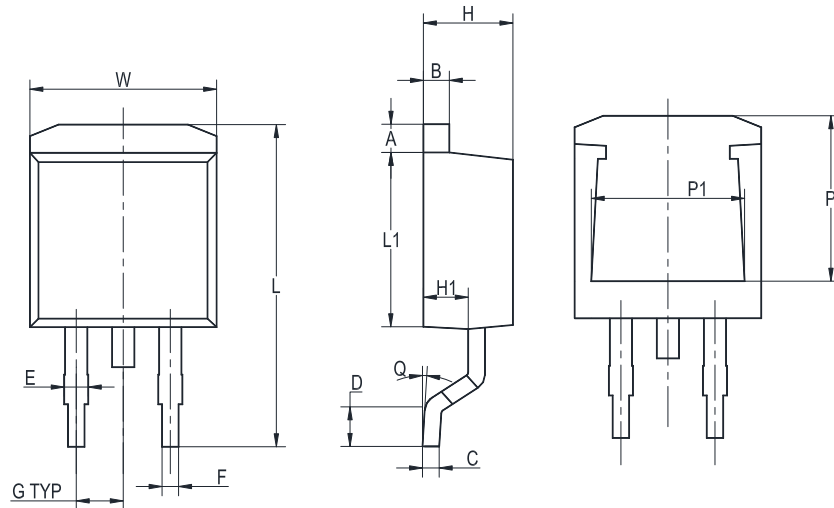


Fig.3-2 Avalanche waveform



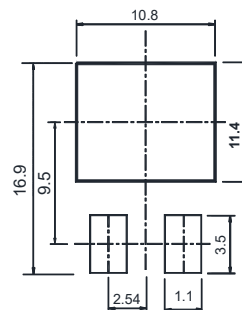
Package Outline (Dimensions in mm)

TO-263



UNIT	A	B	C	D	E	F	G	W	H	H1	L	L1	Q	P	P1
mm	1.5	1.5	0.5	2.60	1.6	0.94	2.54	10.5	4.8	2.9	16.5	8.7	8°	7.6	8.2
	1.1	1.1	0.3	2.15	1.1	0.68	TYP	9.6	4.4	2.5	14.5	8.2	MAX	7.1	7.4

Recommended Soldering Footprint



Packing information

Package	Reel Quantity	Box Quantity	Carton Quantity	Delivery Mode
TO-263	0.8 K / Reel	0.8 K / Box	4K pcs / Carton	Reel

Marking information

" PV65N190 " = Part No.

" ***** " = Date Code Marking

Font type: Arial

